

Power Matters.™

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Overview

Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	V _{CE(sat)}			1.40	V
DC Current Gain	HFE	15.00		60.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			160.00	V
Collector Current (dc)	I _C			16.00	A
Collector-Emitter Voltage (Base Open)	V _{CEO}			140.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			7.00	V
Power Dissipation, Total	P _T			150.00	W

This part can be found in the following product categories:

- ▶ Discretes ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ PNP Transistor
- ▶ Non-Radiation Hardened Devices ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ PNP Transistor

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